

What is claimed is:

1. A wavelength stabilized laser module comprising:
 2 a semiconductor laser;
 3 a temperature calibrating unit to calibrate a temperature
 4 of said semiconductor laser;
 5 a converting unit to convert light emitted from said
 6 semiconductor laser to parallel luminous flux;
 7 a first photoelectric converting unit to receive a part of
 8 said parallel luminous flux and to convert it to an electric
 9 signal;
 10 a filter to receive a part of said parallel luminous flux
 11 and to continuously change its transmittance depending on
 12 wavelengths of said parallel luminous flux;
 13 a second photoelectric converting unit to receive light
 14 transmitted through said filter and to convert it to an electric
 15 signal; and
 16 wherein a control signal, to be used for stabilization,
 17 obtained by computations of said electric signal fed from said
 18 first photoelectric converting unit and said second photoelectric
 19 converting unit, is fed back to said semiconductor laser and/or
 20 said temperature calibrating unit so that said semiconductor
 21 laser is able to stably emit laser light having a reference
 22 wavelength to be used as a target for stabilization of
 23 wavelengths.

1 2. The wavelength stabilized laser module according to
 2 Claim 1, wherein said first photoelectric converting unit and said
 3 second photoelectric converting unit are so configured as to

4 receive backward emitted light from said semiconductor laser.

Sub A2 3. The wavelength stabilized laser module according to

2 Claim 1, wherein said converting unit to convert light emitted
3 from said semiconductor laser to said parallel luminous flux is
4 a lens and wherein one part of said single parallel luminous flux
5 transmitted through said lens is incident on said first
6 photoelectric converting unit and another part of said parallel
7 flux is incident on said filter.

1 4. The wavelength stabilized laser module according to
2 Claim 1, wherein a degree of parallelization of said parallel
3 luminous flux is within $\pm 2^\circ$.

1 5. The wavelength stabilized laser module according to
2 Claim 1, wherein said filter has a transmission characteristic
3 in which transmittance of said filter becomes high or low
4 monotonically depending on wavelengths within a band of
5 wavelengths containing said reference wavelength.

1 6. The wavelength stabilized laser module according to
2 Claim 1, wherein said filter is able to change, by adjusting an
3 angle of incidence, a gradient of changes in transmittance which
4 changes depending on wavelengths.

1 7. The wavelength stabilized laser module according to
2 Claim 1, wherein said filter has a unimodal transmission
3 characteristic in which transmittance of said filter becomes
4 maximum and minimum in a band of wavelengths not containing said

reference wavelength.

8. The wavelength stabilized laser module according to Claim 1, wherein said filter is a multilayer filter made up of dielectric multilayers formed on a transparent substrate.

9. The wavelength stabilized laser module according to Claim 1, wherein said filter is an etalon-type filter exhibiting a transmittance period in which transmittance of said filter becomes maximum and minimum repeatedly at a constant interval of wavelengths.

10. The wavelength stabilized laser module according to Claim 9, wherein said semiconductor laser is a wavelength tunable semiconductor laser that is able to emit light having a plurality of wavelengths which change depending on temperatures and said interval of wavelengths in said transmittance period of said etalon-type filter is set by an equation:

$$D = (1 - \text{Tetalon} / \text{TLD}) \times D0 \quad (1)$$

where said "D" represents said interval of wavelengths in said transmittance period of said etalon-type filter, said "D0" represents an interval of said plurality of wavelengths of light emitted from said semiconductor laser, said "Tetalon" represents an amount of a change in a central wavelength occurring when a temperature of said etalon-type filter changes by 1°C and said "TLD" represents an amount of a change in an oscillation wavelength occurring when a temperature of said semiconductor laser changes by 1°C, however, said central wavelength represents one wavelength that causes said transmittance to be maximum.

new
1 11. The wavelength stabilized laser module according to
2 Claim 1, wherein said filter is made up of a transparent material
3 having reflectivity being higher than that of silica glass.

1 12. The wavelength stabilized laser module according to
2 Claim 11, wherein said transparent material is a silicon based
3 material.

1 13. The wavelength stabilized laser module according to
2 Claim 1, wherein said filter is fixed to said second photoelectric
3 converting unit.

1 14. The wavelength stabilized laser module according to
2 Claim 8, wherein said filter is formed on a light receiving surface
3 of said second photoelectric converting unit by a coating method.

1 15. The wavelength stabilized laser module according to
2 Claim 1, wherein said first photoelectric converting unit and said
3 second photoelectric converting unit are placed in parallel on
4 a holding substrate and make up an array-shaped optical detector.

1 16. The wavelength stabilized laser module according to
2 Claim 1, wherein a light receiving surface of said first
3 photoelectric converting unit is placed in a tilt manner relative
4 to an optical axis of incident light.

new
1 17. The wavelength stabilized laser module according to
2 Claim 1, wherein said semiconductor laser has a configuration of
3 a device integrated with an electro-absorption-type

4 semiconductor optical modulator.

1 18. The wavelength stabilized laser module according to
2 Claim 1, wherein said temperature calibrating unit is a Peltier
3 device.

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1 19. The wavelength stabilized laser module according to
2 Claim 1, further comprising an optical fiber used as a device
3 through which laser light is output and a single case housing,
4 at least, said semiconductor laser, said temperature calibrating
5 unit, said converting unit for said light conversion to said
6 parallel luminous flux, said filter and said first photoelectric
7 converting unit and said second photoelectric converting unit.